## What is claimed is:

 A vertical cavity surface emitting laser (VCSEL), comprising: at least one quantum well having a depth of at least 40 meV and comprised of InGaAsSb;

barrier layers sandwiching said at least one quantum well; and confinement layers sandwiching said barrier layers.

- 2. The VCSEL of claim 1 wherein said barrier layers are comprised of GaAsN.
- 3. The VCSEL of claim 1 wherein said barrier layers are comprised of GaAsP.
- 4. The VCSEL of claim 1 wherein said barrier layers are comprised of AlGaAs.
- 5. The VCSEL of claim 1 wherein said confinement layers are comprised of AlGaAs.
- 6. The VCSEL of claim 1 wherein said quantum well is up to and including 50 Å in thickness.
- 7. The VCSEL of claim 2 wherein said confinement layers are comprised of AlGaAs.
- 8. The VCSEL of claim 7 wherein said quantum well is up to and including 50 Å in thickness.
- 9. The VCSEL of claim 3 wherein said confinement layers are comprised of AlGaAs.

- 10. The VCSEL of claim 9 wherein said quantum well is up to and including 50 A in thickness.
- 11. The VCSEL of claim 4 wherein said confinement layers are comprised of AlGaAs.
- 12. The VCSEL of claim 11 wherein said quantum well is up to and including 50 Å in thickness.
- 13. The VCSEL of claim 1 wherein said at least one quantum well further comprises >1% N.
- 14. The VCSEL of claim 13 wherein said quantum well is up to and including 50 Å in thickness.
- 15. The VCSEL of claim 13 wherein said barrier layers are comprised of GaAsN.
- 16. The VCSEL of claim 15 wherein said quantum well is up to and including 50  $\hbox{\normalfont\AA}$  in thickness.
- 17. The VCSEL of claim 13 wherein said barrier layers are comprised of GaAsP.
- 18. The VCSEL of claim 17 wherein said quantum well is up to and including 50 Å in thickness.
- 19. The VCSEL of claim 13 wherein said barrier layers are comprised of AlGaAs.

- 20. The VCSEL of claim 19 wherein said quantum well is up to and including 50 Å in thickness.
- 21. The VCSEL of claim 13 wherein said confinement layers are comprised of AlGaAs.
- 22. The VCSEL of claim 21 wherein said quantum well is up to and including 50 Å in thickness.
- 23. The VCSEL of claim 15 wherein said confinement layers are comprised of AlGaAs.
- 24. The VCSEL of claim 23 wherein said quantum well is up to and including 50 Å in thickness.
- 25. The VCSEL of claim 17 wherein said confinement layers are comprised of AlGaAs.
- 26. The VCSEL of claim 25 wherein said quantum well is up to and including 50 Å in thickness.
- 27. The VCSEL of claim 19 wherein said confinement layers are comprised of AlGaAs.
- 28. The VCSEL of claim 27 wherein said quantum well is up to and including 50 Å in thickness.
- 29. The VCSEL of claim 1 wherein said at least one quantum well further comprises N.
- 30. The VCSEL of claim 29 wherein said quantum well is up to and including 50 Å in thickness.

- 31. The VCSEL of claim 29 wherein said barrier layers are comprised of GaAsN.
- 32. The VCSEL of claim 31 wherein said quantum well is up to and including 50 Å in thickness.
- 33 32. The VCSEL of claim 29 wherein said barrier layers are comprised of GaAsP.
- 34 38. The VCSEL of claim 32 wherein said quantum well is up to and including 50 Å in thickness.
- 35 34. The VCSEL of claim 29 wherein said barrier layers are comprised of AlGaAs.
- 36 25. The VCSEL of claim 34 wherein said quantum well is up to and including 50 Å in thickness.
- 37 36. The VCSEL of claim 29 wherein said confinement layers are comprised of AlGaAs.
- 38 36. The VCSEL of claim 36 wherein said quantum well is up to and including 50 Å in thickness.
- 38. The VCSEL of claim 31 wherein said confinement layers are comprised of AlGaAs.
- 10 39. The VCSEL of claim 38 wherein said quantum well is up to and including 50 Å in thickness.

- 40. The VCSEL of claim 34 wherein said confinement layers are comprised of AlGaAs.
- (1) A1. The VCSEL of claim 40 wherein said quantum well is up to and including 50 Å in thickness.
- The VCSEL of claim 36 wherein said confinement layers are comprised of AlGaAs.
- The VCSEL of claim 42 wherein said quantum well is up to and including 50 Å in thickness.